

## TGD N-Channel Enhancement Mode Power MOSFET

### Description

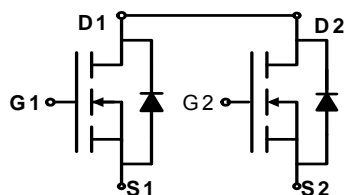
The TGD2007N uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

### General Features

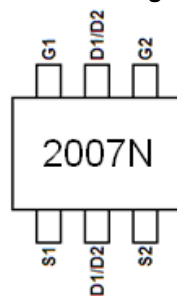
- $V_{DS} = 20V, I_D = 6.5A$   
 $R_{DS(ON)} < 27m\Omega @ V_{GS}=2.5V$   
 $R_{DS(ON)} < 22m\Omega @ V_{GS}=4.5V$
- High power and current handling capability
- Lead free product is acquired
- Surface mount package

### Application

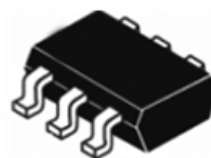
- Battery protection
- Load switch
- Power management



Schematic diagram



pin assignment



SOT23-6L top view

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
2007N	TGD2007N	SOT23-6L	Ø330mm	12mm	3000 units

### Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Drain Current-Continuous	$I_D$	6.5	A
Drain Current-Pulsed <sup>(Note 1)</sup>	$I_{DM}$	25	A
Maximum Power Dissipation	$P_D$	1.5	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	$^\circ C$

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient <sup>(Note 2)</sup>	$R_{\theta JA}$	83	$^\circ C/W$
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### Electrical Characteristics ( $T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						



Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	20	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =6A	-	14.5	22	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =5.5A	-	19	27	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =6A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, F=1.0MHz	-	900	-	PF
Output Capacitance	C <sub>oss</sub>		-	220	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	100	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =6A V <sub>GS</sub> =4.5V, R <sub>GEN</sub> =6Ω	-	10	20	nS
Turn-on Rise Time	t <sub>r</sub>		-	11	25	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	35	70	nS
Turn-Off Fall Time	t <sub>f</sub>		-	30	60	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =6A, V <sub>GS</sub> =4.5V	-	12	15	nC
Gate-Source Charge	Q <sub>gs</sub>		-	2.3	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =6A	-	-	1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	6.5	A

### Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

## Typical Electrical and Thermal Characteristics

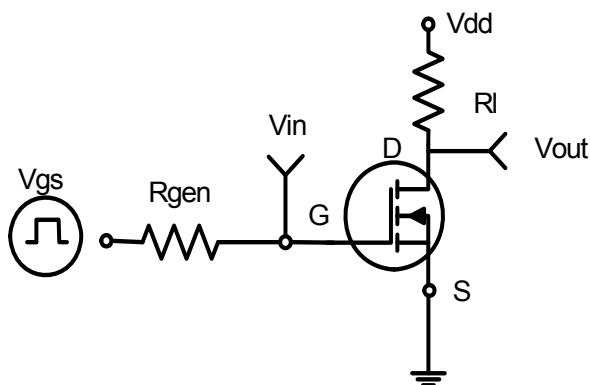


Figure 1: Switching Test Circuit

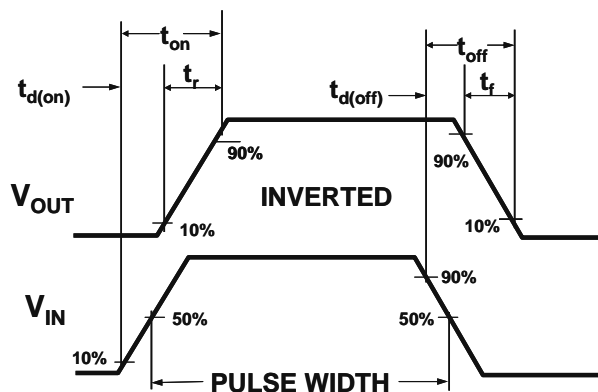


Figure 2: Switching Waveforms

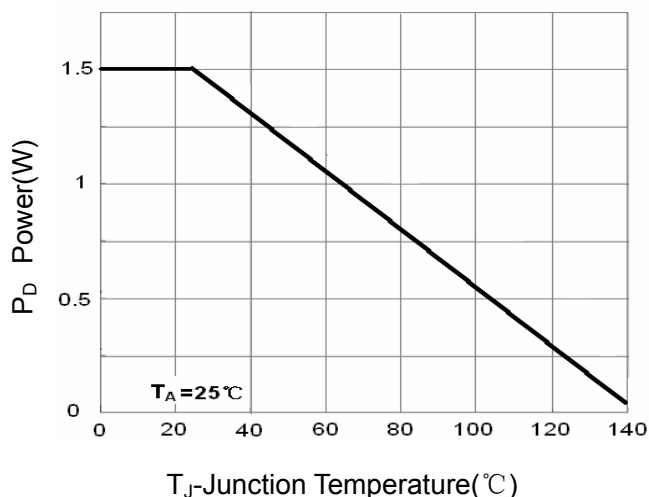


Figure 3 Power Dissipation

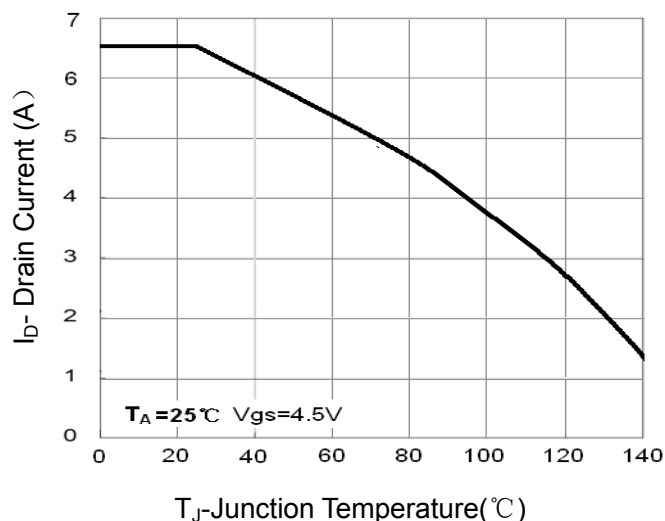


Figure 4 Drain Current

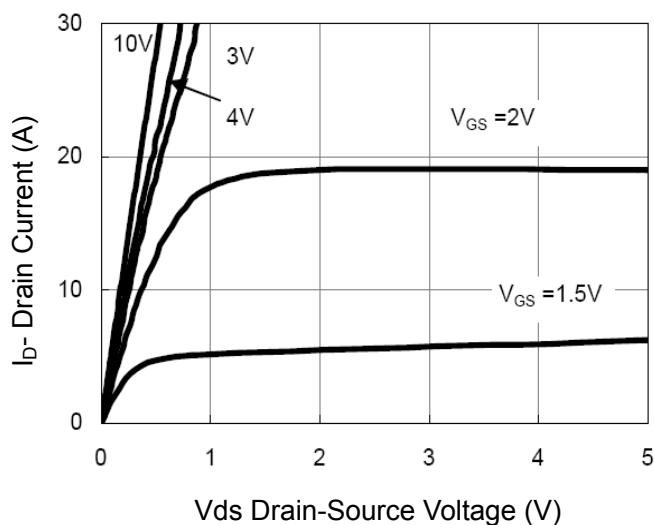


Figure 5 Output Characteristics

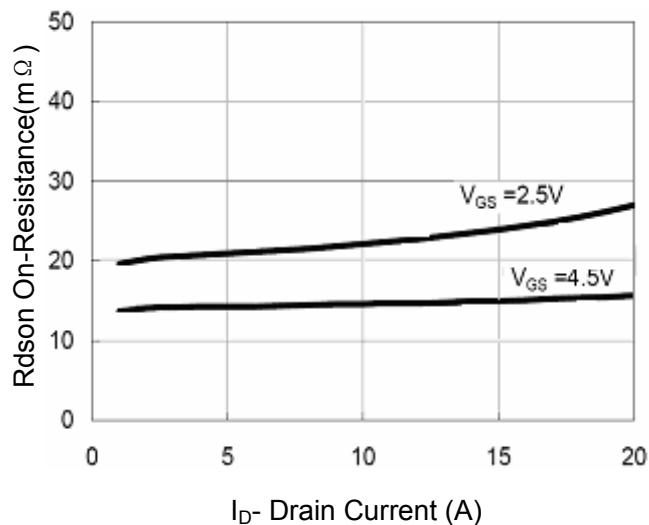


Figure 6 Drain-Source On-Resistance

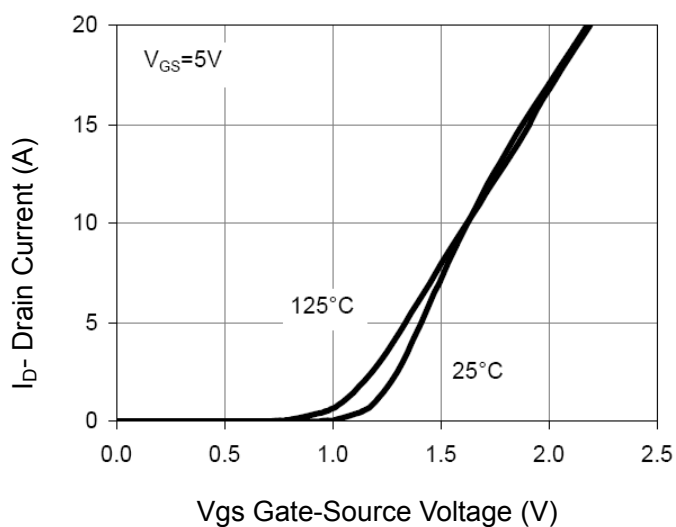


Figure 7 Transfer Characteristics

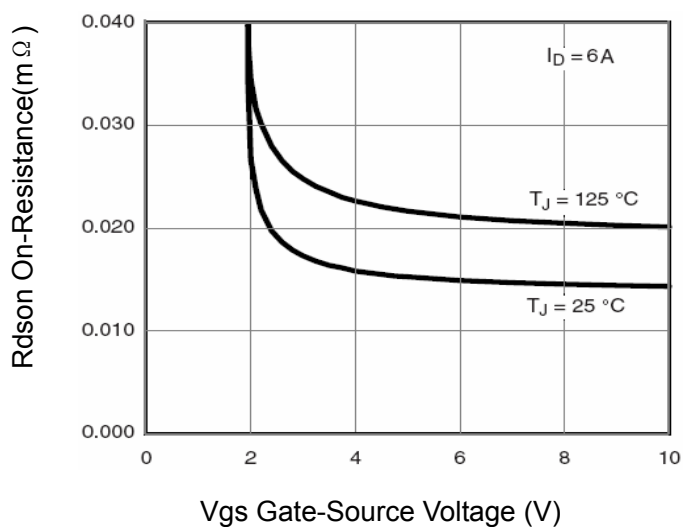


Figure 9 Rdson vs Vgs

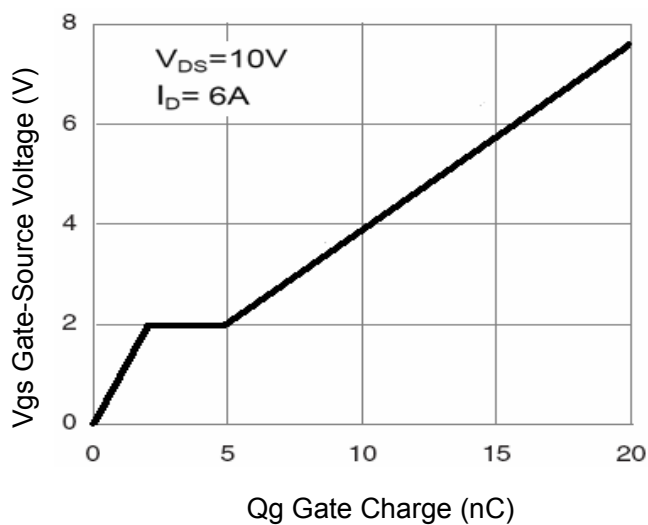


Figure 11 Gate Charge

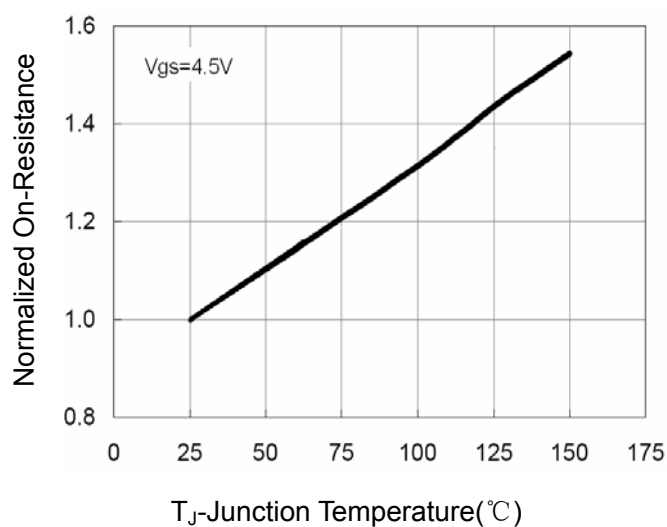


Figure 8 Drain-Source On-Resistance

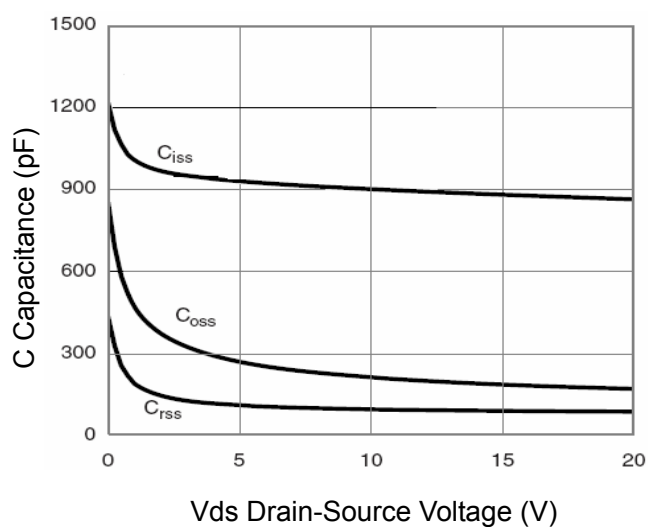


Figure 10 Capacitance vs Vds

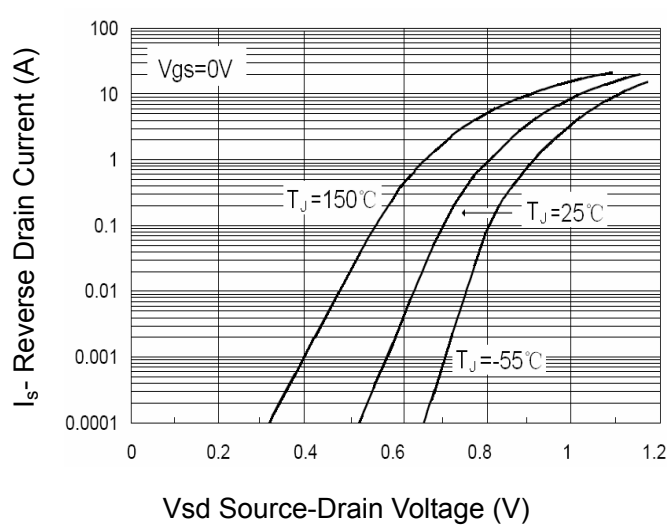


Figure 12 Source- Drain Diode Forward

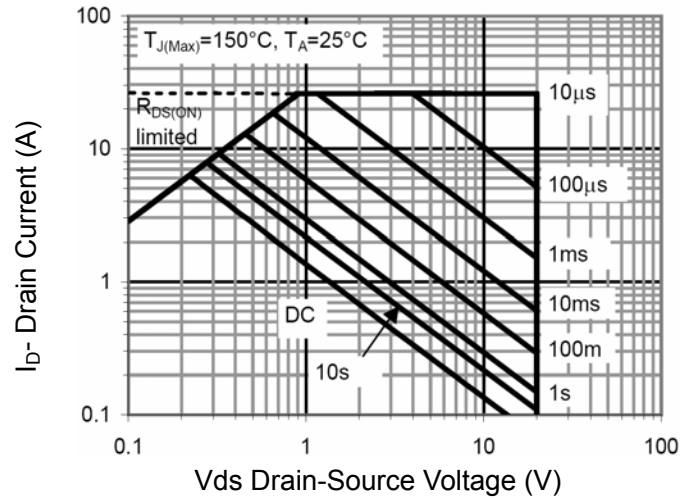


Figure 13 Safe Operation Area

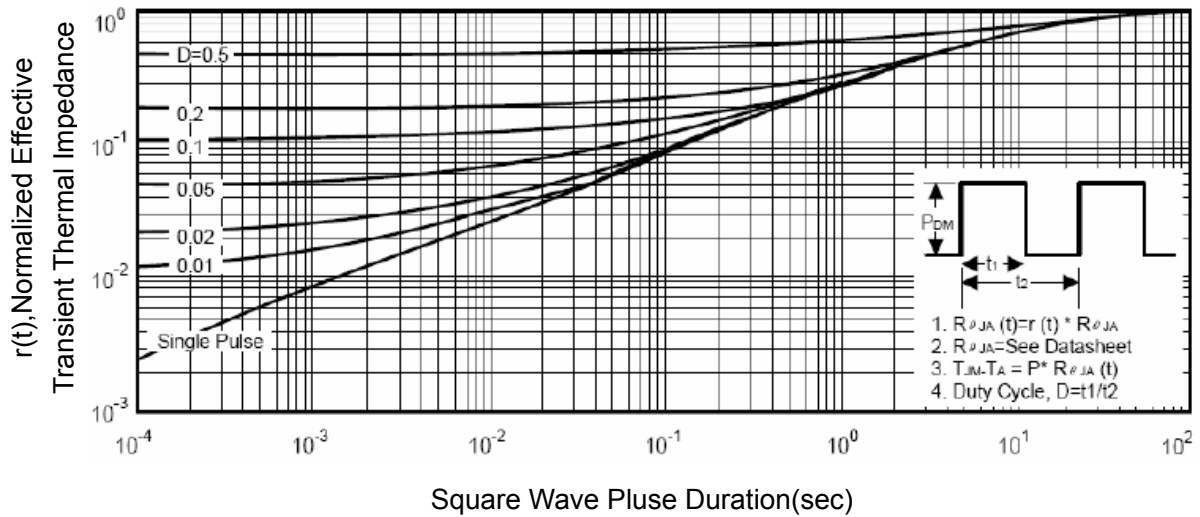
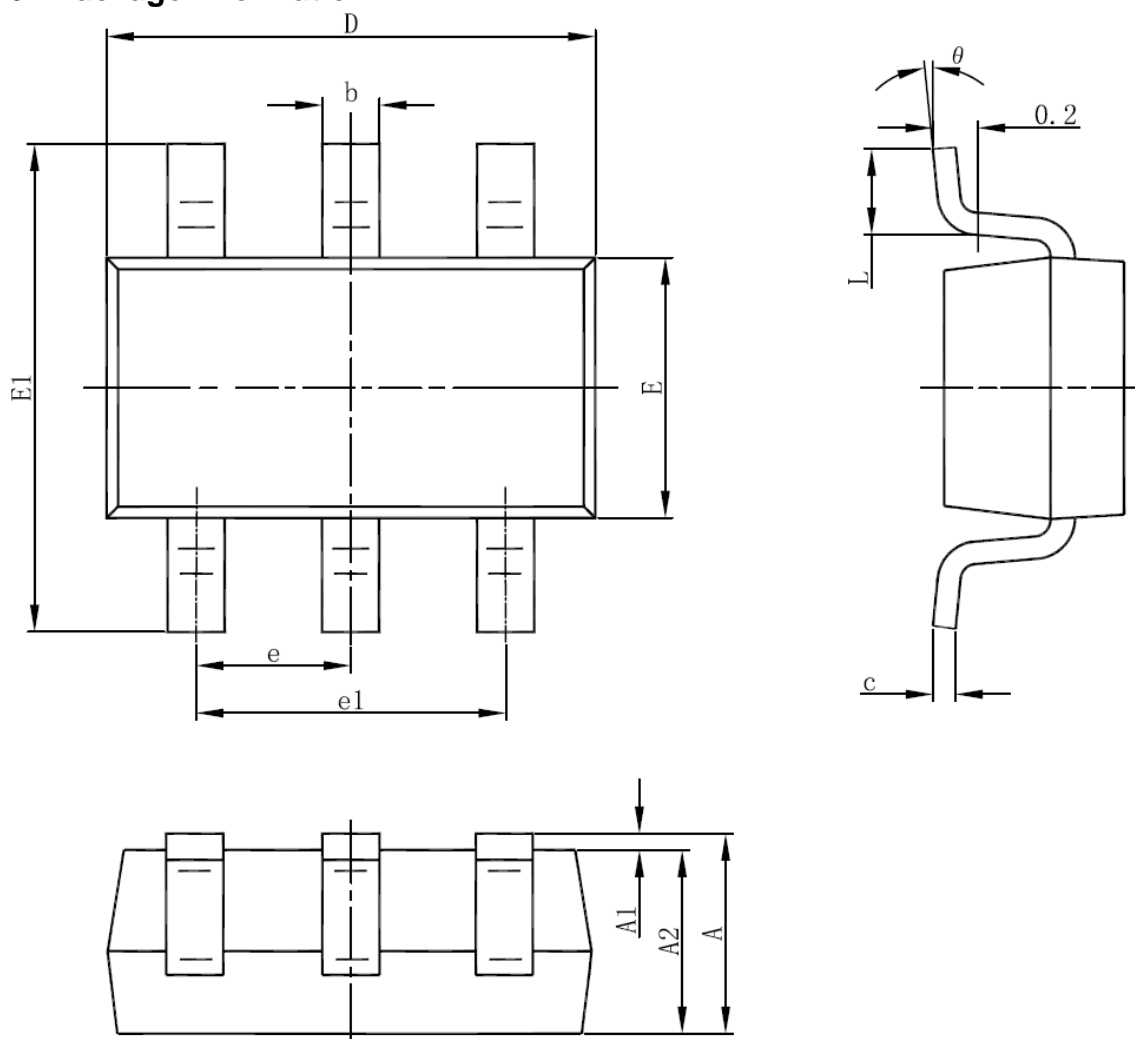


Figure 14 Normalized Maximum Transient Thermal Impedance

## SOT23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°